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NOTICE OF ALLOWANCE AND FEE(S) DUE

65913	7590	02/06/2009		EXAM	EXAMINER	
NXP, B.V.			CHHAYA, SWAPNEEL			
	LECTUAL I	PROPERTY DEPARTMENT		ART UNIT	PAPER NUMBER	
M/\$41-\$1						

1109 MCKAY DRIVE SAN JOSE, CA 95131

 APPLICATION NO.
 FILING DATE
 FIRST NAMED INVENTOR
 ATTORNEY DOCKET NO.
 CONTRIMATION NO.

 10/554,067
 10/21/2005
 Rebba El-Futhane
 FR03 0044 USI
 8293

TITLE OF INVENTION: SEMICONDUCTOR DEVICE COMPRISING EXTENSIONS PRODUCED FROM MATERIAL WITH A LOW MELTING POINT

POINT

APPLN. TYPE	SMALL ENTITY	ISSUE FEE DUE	PUBLICATION FEE DUE	PREV. PAID ISSUE FEE	TOTAL FEE(S) DUE	DATE DUE
nonprovisional	NO	\$1510	\$300	\$0	\$1810	05/06/2009

THE APPLICATION IDENTIFIED ABOVE HAS BEEN EXAMINED AND IS ALLOWED FOR ISSUANCE AS A PATENT. PROSECUTION ON THE MERITS IS CLOSED. THIS NOTICE OF ALLOWANCE IS NOT A GRANT OF PATENT RIGHTS. THIS APPLICATION IS SUBJECT TO WITHDRAWAL FROM ISSUE AT THE INITIATIVE OF THE OFFICE OR UPON PETITION BY THE APPLICANT. SEE 37 CFR 1.313 AND MPEP 1308.

THE ISSUE FEE AND PUBLICATION FEE (IF REQUIRED) MUST BE PAID WITHIN THREE MONTHS FROM THE MAILING DATE OF THIS NOTICE OR THIS APPLICATION SHALL BE REGARDED AS ABANDONED. THIS STATUTORY PERIOD CANNOT BE EXTENDED. SEE 35 U.S.C. 1SI. THE ISSUE FEE DUE INDICATED ABOVE DOES NOT REFLECT A CREDIT FOR ANY PREVIOUSLY PAID ISSUE FEE IN THIS APPLICATION. IF AN ISSUE FEE HAS PREVIOUSLY BEEN PAID IN THIS APPLICATION (AS SHOWN ABOVE), THE RETURN OF PART B OF THIS FORM WILL BE CONSIDERED A REQUEST TO REAPPLY THE PREVIOUSLY PAID ISSUE FEE TOWARD THE ISSUE FEE NOW DUE.

HOW TO REPLY TO THIS NOTICE:

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If the SMALL ENTITY is shown as YES, verify your current SMALL ENTITY status:

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B. If the status above is to be removed, check box 5b on Part B - Fee(s) Transmittal and pay the PUBLICATION FEE (if required) and twice the amount of the ISSUE FEE shown above, or

If the SMALL ENTITY is shown as NO:

A. Pay TOTAL FEE(S) DUE shown above, or

B. If applicant claimed SMALL ENTITY status before, or is now claiming SMALL ENTITY status, check box 5a on Part B - Fee(s) Transmittal and pay the PUBLICATION FEE (if required) and 1/2 the ISSUE FFE shown above.

II. PART B - FEE(S) TRANSMITTAL, or its equivalent, must be completed and returned to the United States Patent and Trademark Office (USPTO) with your ISSUE FEE and PUBLICATION FEE (if required). If you are charging the fee(s) to your deposit account, section "4b" of Part B - Fee(s) Transmittal should be completed and an extra copy of the form should be submitted. If an equivalent of Part B is filed, a request to reapply a previously paid issue fee must be clearly made, and delays in processing may occur due to the difficulty in recognizing the paper as an equivalent of Part B.

III. All communications regarding this application must give the application number. Please direct all communications prior to issuance to Mail Stop ISSUE FEE unless advised to the contrary.

IMPORTANT REMINDER: Utility patents issuing on applications filed on or after Dec. 12, 1980 may require payment of maintenance fees. It is patentee's responsibility to ensure timely payment of maintenance fees when due.

PART B - FEE(S) TRANSMITTAL

Complete and send this form, together with applicable fee(s), to: Mail Mail Stop ISSUE FEE Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

or <u>Fax</u> (571)-273-2885

INSTRUCTIONS: This appropriate. All further c indicated unless correcte maintenance fee notificate	form should be used for correspondence including d below or directed oth ions.	or tran g the ierwise	nsmitting the ISSU Patent, advance on in Block 1, by (a					nould be completed where correspondence address as rate "FEE ADDRESS" for
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NXP, B.V. NXP INTELLEC M/S41-SJ	7590 02/06 CTUAL PROPERT		PARTMENT	I he Stat add tran	reby certify that th	is Feet	of Mailing or Transs s) Transmittal is being ficient postage for firs ISSUE FEE address I) 273-2885, on the da	mission deposited with the United t class mail in an envelope above, or being facsimile ate indicated below.
1109 MCKAY D SAN JOSE, CA								(Depositor's name)
51-11-10-00A, C11-								(Signature)
								(Date)
APPLICATION NO.	FILING DATE			FIRST NAMED INVENTOR	:	ATTO	RNEY DOCKET NO.	CONFIRMATION NO.
10/554,067	10/21/2005			Rebha El-Farhane		I	R03 0044 US1	8293
TITLE OF INVENTION POINT	: SEMICONDUCTOR	DEVI	CE COMPRISING	EXTENSIONS PROD	UCED FROM MA	TERI/	L WITH A LOW M	ELTING
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nonprovisional	NO		\$1510	\$300	\$0		\$1810	05/06/2009
EXAMI	INER		ART UNIT	CLASS-SUBCLASS	1			
CHHAYA, S'	WAPNEEL		2895	257-288000	,			
"Fee Address" indi- PTO/SB/47; Rev 03-02 Number is required. 3. ASSIGNEE NAME AN	ondence address (or Cha v/122) attached. cation (or "Fee Address' 2 or more recent) attach ND RESIDENCE DATA ess an assignee is identi in 37 CFR 3.11. Comp	nge of 'Indica ed. Usa	Correspondence ation form e of a Customer		o 3 registered pater vely, le firm (having as a agent) and the nam rneys or agents. If printed. pe)	memb es of u no nan	er a 2 p to e is 3 lentified below, the do	ocument has been filed for
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	SMALL ENTITY statu	s. See	37 CFR 1.27.	b. Applicant is no lon				
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65913	7590	02/06/2009		EXAMINER			
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NXP INTELLE	CTUAL P	ROPERTY DE	ART UNIT	PAPER NUMBER			
M/S41-SJ 1109 MCKAY	DRIVE		2895 DATE MAII ED: 02/06/200	9			

Determination of Patent Term Adjustment under 35 U.S.C. 154 (b)

(application filed on or after May 29, 2000)

The Patent Term Adjustment to date is 213 day(s). If the issue fee is paid on the date that is three months after the mailing date of this notice and the patent issues on the Tuesday before the date that is 28 weeks (six and a half months) after the mailing date of this notice, the Patent Term Adjustment will be 213 day(s).

If a Continued Prosecution Application (CPA) was filed in the above-identified application, the filing date that determines Patent Term Adjustment is the filing date of the most recent CPA.

Applicant will be able to obtain more detailed information by accessing the Patent Application Information Retrieval (PAIR) WEB site (http://pair.uspto.gov).

Any questions regarding the Patent Term Extension or Adjustment determination should be directed to the Office of Patent Legal Administration at (571)-272-7702. Questions relating to issue and publication fee payments should be directed to the Customer Service Center of the Office of Patent Publication at 1-(888)-786-0101 or (571)-272-4200.

Application No. Applicant(s) 10/554 067 EL-FARHANE, REBHA Notice of Allowability Examiner Art Unit SWAPNEEL CHHAYA 2895 -- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308. This communication is responsive to Appeal brief 12/05/2008. 2. The allowed claim(s) is/are 1-11. 3. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). b) ☐ Some* c) ☐ None of the: 1. A Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)). * Certified copies not received: _____. Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 4. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient. CORRECTED DRAWINGS (as "replacement sheets") must be submitted. (a) Including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d). 6. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL. Attachment(s) 1. | Notice of References Cited (PTO-892) 5. Notice of Informal Patent Application 2. Notice of Draftperson's Patent Drawing Review (PTO-948) Interview Summary (PTO-413), Paper No./Mail Date Information Disclosure Statements (PTO/SB/08). 7. X Examiner's Amendment/Comment Paper No./Mail Date 4. T Examiner's Comment Regarding Requirement for Deposit 8. X Examiner's Statement of Reasons for Allowance

of Biological Material

9. ☐ Other .

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EXAMINER'S AMENDMENT

 An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Robert Crawford on 1/30 at 1:33 p.m..

The application has been amended as follows:

1. A semiconductor device comprising:

a gate electrode and a gate insulating layer produced on a part of the surface of a substrate of a first semiconductor material having a given melting point, and surrounded by an insulating spacer in a plane parallel to the surface of the substrate, the gate insulating layer being disposed between the substrate and the gate electrode, and a source region and a drain region situated under the surface of the substrate at the level of two opposite sides of the gate electrode, respectively, each region containing electrical carriers of the same given type, with respective first concentrations, and each region comprising a portion of a second semiconductor material disposed on the substrate below the level of the gate insulating layer in a direction perpendicular to the surface of the substrate, each portion of second material extending at least partially between the substrate and the spacer, <u>under at least a portion of the spacer and</u> substantially as far as a limit coming in line, in said perpendicular direction, with one side of the gate electrode, said portions of second material being doped with doping

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elements in order to create electrical carriers of said given type with second concentrations less than said first concentrations, and said portions of second material having a melting point lower than the melting point of the first material.

- 2. A device as claimed in claim 1, in which said portions of second material have an ability to absorb a light radiation greater than the absorption ability of the first material for the same light radiation.
- 3. A device as claimed in claim 1, in which the first material is based on silicon and the second material is based on germanium or based on an alloy of silicon and germanium.
- 4. A device as claimed in claim 1, also comprising two encapsulation portions of said second material, disposed respectively over the portions of second material, on a side opposite to the substrate.
- 5. A device as claimed in claim 4, in which each encapsulation portion extends between the spacer and the portion of second material above which said encapsulation portion is disposed, substantially as far as a limit situated in line, in said direction perpendicular to the surface of the substrate, with the side of the gate electrode corresponding to said second encapsulation portion.
- 6. A device as claimed in claim 1, characterized in that said device is an MOS transistor.
- 7. A method of manufacturing a semiconductor device, comprising the following steps:
- a) a gate insulating layer is formed on a part of a surface of a substrate of a first semiconductor material having a given melting point;
- b) a gate electrode is formed on top of the gate insulating layer:

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 c) an insulating spacer is formed, disposed around the gate insulating layer and the gate electrode, parallel to the surface of the substrate;

- d) two surface films of the first material are removed respectively in two lateral parts of the surface of the substrate situated on two opposite sides of the surface part of the substrate carrying the gate insulating layer and the gate electrode, each lateral part extending between the substrate and the spacer substantially as far as a limit coming in line with one of the opposite sides of the gate electrode, in a direction perpendicular to the surface of the substrate:
- e) a source region and a drain region are formed, each region being situated below the surface of the substrate at a level of said two lateral parts of the surface of the substrate, respectively, each region containing electrical carriers of the same given type with respective first concentrations;
- f) there is formed on the substrate, in each lateral part, a portion of a second semiconductor material <u>under at least a portion of the spacer and</u> substantially as far as a limit coming in line, in said perpendicular direction, with the opposite side of the gate electrode corresponding to said lateral part, said portions of second material containing doping elements in order to create electrical carriers of the given type, and having a melting point lower than the melting point of the first material;
- g) the portions of second material are heated to a temperature intermediate between the respective melting points of the first and second materials, so that the portions of second material contain electrical carriers with second concentrations lower than said first concentrations.

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8. A method as claimed in claim 7, according to which,

during step g), said portions of second material are heated using a laser beam.

- 9. A method as claimed in claim 7, according to which, after
- step f), encapsulation portions are deposited respectively on top of said portions of second material, on a side opposite to the substrate.
- A method as claimed in claim 7, according to which step e) is performed before step d).
- 11. A method as claimed in claim 7, wherein steps a) through g) are performed successively.
- 2. The following is an examiner's statement of reasons for allowance: the closest prior art of note is Wieczorek et al. (U.S. Patent 6274894), this reference, however, does not disclose nor make obvious the limitation of the second material extending at least partially under the spacer as the material ends at the end of the spacer. Prior to the examiner's amendment, the interpretation of the "second material" of the reference was sufficient to reject the instant application due to the broadest reasonable interpretation of the word substantially as written in the claim language of the instant application in claims 1 and 7. The language has been changed through this amendment to further limit the independent claims.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably Application/Control Number: 10/554,067

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accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to SWAPNEEL CHHAYA whose telephone number is (571)270-1434. The examiner can normally be reached on Monday- Thursday 9:30-7:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Drew Richards can be reached on 571-272-1736. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

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/N. Drew Richards/ Supervisory Patent Examiner, Art Unit 2895